

Drafts  Pending

 Active  
 L1: (1) ("5814557"). PN.  
 L2: (1) ("5256274"). PN.

 L3: (1583972) heat or heats or heated or heating  
 L4: (151341) anneal or anneals or annealed or annealing

 L5: (0) 12 and 14  
 L6: (1) 12 and 13

 L7: (56603) electroplat\$ or electrodeposit\$  
 L8: (13537) (electrolyt\$ or electrochem\$) near2 deposit\$  
 L9: (15970) (electrolyt\$ or electrochem\$) near2 deposit\$ (plate or plates or plated or plating)

 L10: (73627) 17 or 18 or 19  
 L11: (486440) copper or Cu

 L12: (26527) 110 same 111  
 L13: (3886) 112 and 14

 L14: (210263) wafer or wafers  
 L15: (1928) 113 and 114

 L16: (975) 112 same 14  
 L17: (544) 116 and 114

Failed

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116 and 114				

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BRS Form		IS&FT Form		Image		Text		HTML	
Current OR		Current XRef		Inventor		U		S	
Document ID	Issue Date	Pages	Title			C	P	1	3
1 US 2005000357920060105	15	15	Interconnects with direct metalization and conductive polymer	438/639	Sir; Jiuu Hann	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2 US 2006000354620060105			Highly compliant plate for wafer bonding	438/455	438/457	Kobrinsky; Mauro J. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3 US 2006000354720060105			Highly compliant plate for wafer bonding	438/455	438/457	Kobrinsky; Mauro J. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4 US 2006000348620060105			Plasma treatment method for electromigration reduction	438/76		Iai; Jane-Bai et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5 US 2005028778520051229			Method of stacking wafers with anisotropic conductive adhesive	438/613	257/734	Lee, Kevin J.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6 US 2005028237120051222			Sequential station tool for wet processing of semiconductor wafers	438/597		Patton, Evan E. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7 US 2005026041120051124			Diamond-like carbon films with low dielectric constant and high mechanical	428/408	427/249.7;	Ravi, Kramadhati V.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
8 US 2005024508520051103			Apparatus and method for electrochemically depositing metal on a metal layer	438/687	427/569	Chen, Linlin et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
9 US 2005024507220051103			Method and apparatus for fabricating metal layer	438/628	438/643;	Lee, Hsien-Ming et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
10 US 2005023927820051027			Process of forming a composite diffusion barrier in copper/organic low-k	438/618	438/644	Li, Chao Yong et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
11 US 2005023359120051020			Techniques promoting adhesion of porous low K film to underlying barrier layer	438/706	216/34;	Schmitt, Francimar et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
12 US 2005023083120051020			Multi-stage curing of low K nano-porous films	257/758	216/67;	Schmitt, Francimar et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
					438/781;				

Num:

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